



150V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
450)/	19mΩ @ V _{GS} = 10V	61A
150V	22mΩ @ V _{GS} = 8V	40A

Description

This new generation N-Channel Enhancement Mode MOSFET is designed to minimize $R_{DS(ON)}$ yet maintain superior switching performance. This device is ideal for use in Notebook battery power management and load switch.

Applications

- Motor Control
- DC-DC Converters
- Power Management

Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Thermally Efficient Package-Cooler Running Applications
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- <1.1mm Package Profile Ideal for Thin Applications (PowerDI[®])
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/guality/product-definitions/

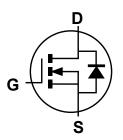
Mechanical Data

- Case: PowerDI5060-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminal Finish Matte Tin Annealed over Copper Lead-Frame.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)

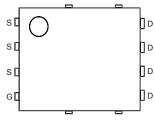
Site 1:



Top View Bottom View



Internal Schematic



Top View Pin Configuration

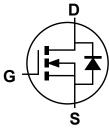


PowerDI5060-8 (SWP) (Type UX)

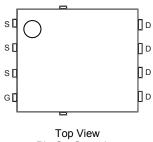


Top View

Bottom View



Internal Schematic



Pin Configuration



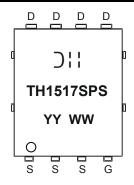
Ordering Information (Note 4)

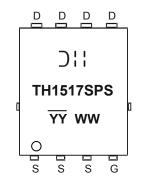
Part Number	Case	Packaging
DMTH15H017SPS-13	PowerDI5060-8	2,500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information





TH1517SPS = Product Type Marking Code
YYWW or YYWW = Date Code Marking
YY or YY = Last Two Digits of Year (ex: 20 = 2020)
WW = Week Code (01 to 53)

Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	150	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current \/ = 10\/ (Note 6)	Steady	T _A = +25°C	- I _D	11	- A
Continuous Drain Current V _{GS} = 10V (Note 6)	State	T _A = +100°C		7	
Continuous Dusin Cument / _ 40// (Note 7)	Steady	T _C = +25°C		61	A
Continuous Drain Current V _{GS} = 10V (Note 7)	State	T _C = +100°C	- I _D	40	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	250	Α		
Maximum Continuous Body Diode Forward Current			Is	61	Α
Pulsed Body Diode Current (10µs Pulse, Duty Cycle = 1%)			I _{SM}	250	Α
Avalanche Current (Note 8), L = 3mH			I _{AS}	14.4	А
Avalanche Energy (Note 8), L = 3mH			E _{AS}	311	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	97	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	3.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	47	°C/W
Total Power Dissipation (Note 7)	T _C = +25°C	P _D	107	W
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	1.4	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +175	°C

Notes:

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.



Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

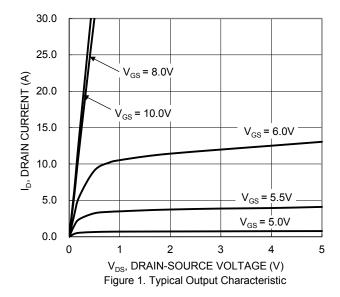
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	150	_	_	V	V _{GS} = 0V, I _D = 10mA	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	V _{DS} = 120V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	V _{GS} = ±20V, V _{DS} = 0V	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	2	1	4	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	0	_	14	19	mΩ	V _{GS} = 10V, I _D = 20A	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	16	22	11122	V _{GS} = 8V, I _D = 15A	
Diode Forward Voltage	V_{SD}	_	0.8	1.2	V	V _{GS} = 0V, I _S = 20A	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	_	2344	_		V _{DS} = 75V, V _{GS} = 0V f = 1MHz	
Output Capacitance	Coss	_	213	_	pF		
Reverse Transfer Capacitance	Crss	_	6.9	_			
Gate Resistance	Rg	_	1.8	_	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz	
Total Gate Charge	Qg	_	34	_			
Gate-Source Charge	Q _{gs}	_	12	_	nC	V _{DD} = 75V, I _D = 20A, V _{GS} = 10V	
Gate-Drain Charge	Q _{gd}	_	9	_			
Turn-On Delay Time	t _{D(ON)}	_	13.2	_		V_{DD} = 75V, V_{GS} = 10V, I_{D} = 20A, R_{g} = 6Ω	
Turn-On Rise Time	t _R	_	22.4	_			
Turn-Off Delay Time	t _{D(OFF)}	_	26.3	_	ns		
Turn-Off Fall Time	t _F	_	16.1				
Reverse Recovery Time	t _{RR}	_	69	_	ns	1 004 41/44 4004/	
Reverse Recovery Charge	Q _{RR}	_	196	_	nC	I _F = 20A, di/dt = 100A/μs	

Notes:

^{9.} Short duration pulse test used to minimize self-heating effect.

^{10.} Guaranteed by design. Not subject to product testing.





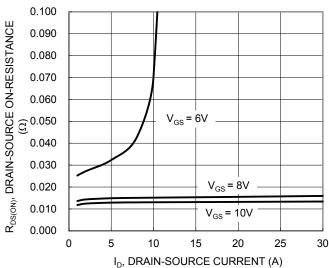


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

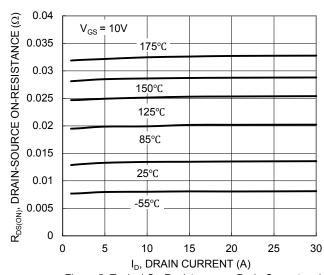
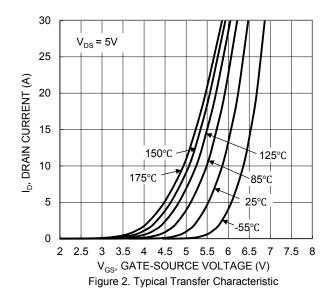
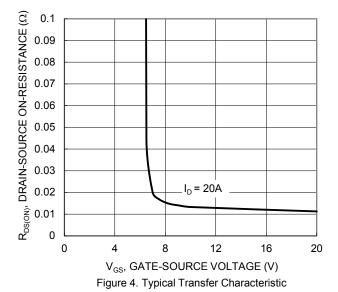


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





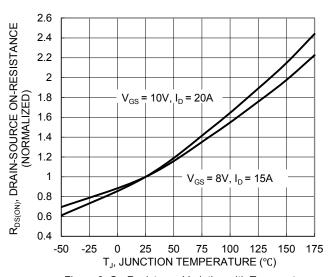


Figure 6. On-Resistance Variation with Temperature



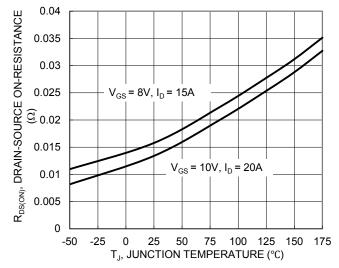


Figure 7. On-Resistance Variation with Temperature

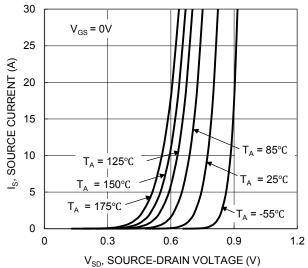
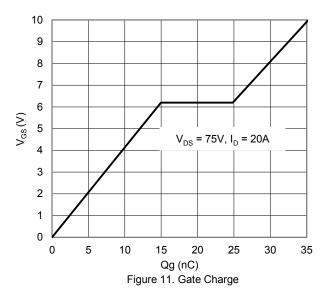


Figure 9. Diode Forward Voltage vs. Current



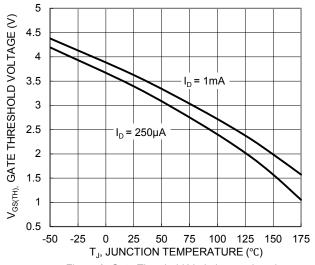


Figure 8. Gate Threshold Variation vs. Junction Temperature

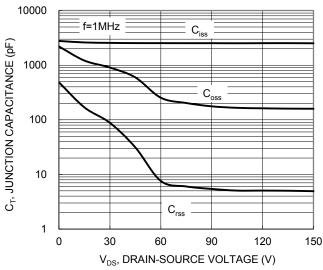
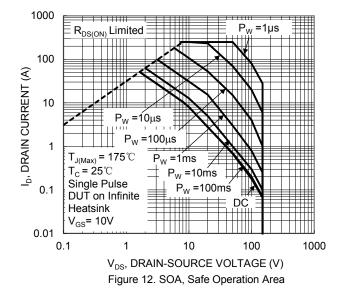


Figure 10. Typical Junction Capacitance





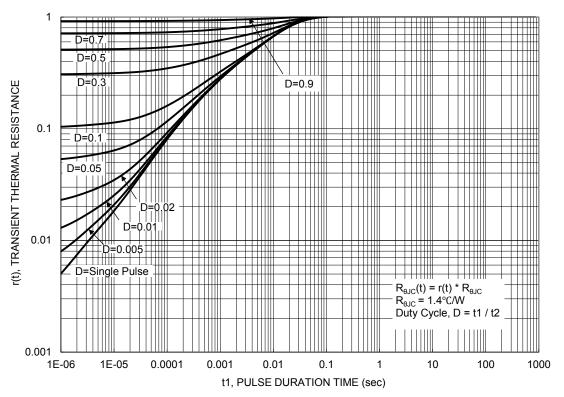


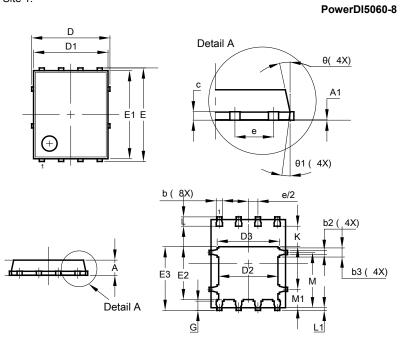
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

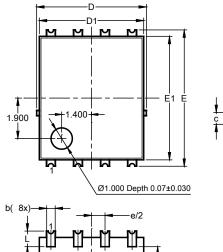
Site 1:

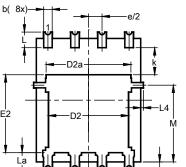


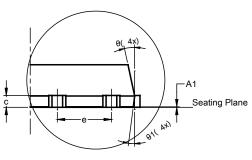
PowerDI5060-8				
Dim	Min	Max	Тур	
Α	0.90	1.10	1.00	
A1	0.00	0.05	-	
b	0.33	0.51	0.41	
b2	0.200	0.350	0.273	
b3	0.40	0.80	0.60	
С	0.230	0.330	0.277	
D	5.15 BSC			
D1	4.70	5.10	4.90	
D2	3.70	4.10	3.90	
D3	3.90	4.30	4.10	
Е	•	3.15 BSC	;	
E1	5.60	6.00	5.80	
E2	3.28	3.68	3.48	
E3	3.99	4.39	4.19	
е	1.27 BSC			
G	0.51	0.71	0.61	
K	0.51	-	-	
L	0.51	0.71	0.61	
L1	0.100	0.200	0.175	
M	3.235	4.035	3.635	
M1	1.00	1.40	1.21	
Θ	10°	12°	11°	
Θ1	6°	8°	7°	
All Dimensions in mm				

Site 2:

PowerDI5060-8 (SWP) (Type UX)







DETAIL A

DETAIL A

PowerDI5060-8 (SWP)				
(Type UX)				
Dim	Min	Max	Тур	
Α	0.90	1.10	1.00	
A1	0	0.05	-	
p	0.30	0.50	0.41	
b2	0.20	0.35	0.25	
b4	().25REF		
C	0.230	0.330	0.277	
D	5	.15 BS	\circ	
D1	4.70	5.10	4.90	
D2	3.56	3.96	3.76	
D2a	3.78	4.18	3.98	
Е	6	.40 BS	\sim	
E1	5.60	6.00	5.80	
E2	3.46	3.86	3.66	
E2a	4.195	4.595	4.395	
е	1.27BSC			
k	1.05		-	
L	0.635	0.835	0.735	
La	0.635	0.835	0.735	
L1	0.200	0.400	0.300	
L1a	0.050REF			
L4	0.025	0.225	0.125	
M	3.205	4.005	3.605	
θ	10°	12°	11°	
θ1	6°	8°	7°	
All Dimensions in mm				

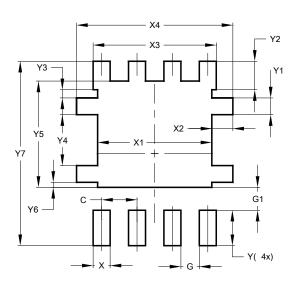


Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

Site 1:

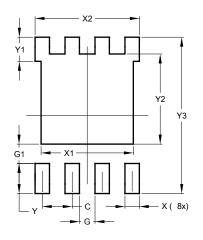
PowerDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
Х3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

Site 2:

PowerDI5060-8 (SWP) (Type UX)



Dimensions	Value		
Dilliensions	(in mm)		
С	1.270		
G	0.660		
G1	0.820		
Х	0.610		
X1	4.100		
X2	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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